

From *Semiconductor Physics and Devices: Basic Principles* (4th Edition), Donald A. Neamen, McGraw Hill, 2012, ISBN 978-0-07-352958-5.

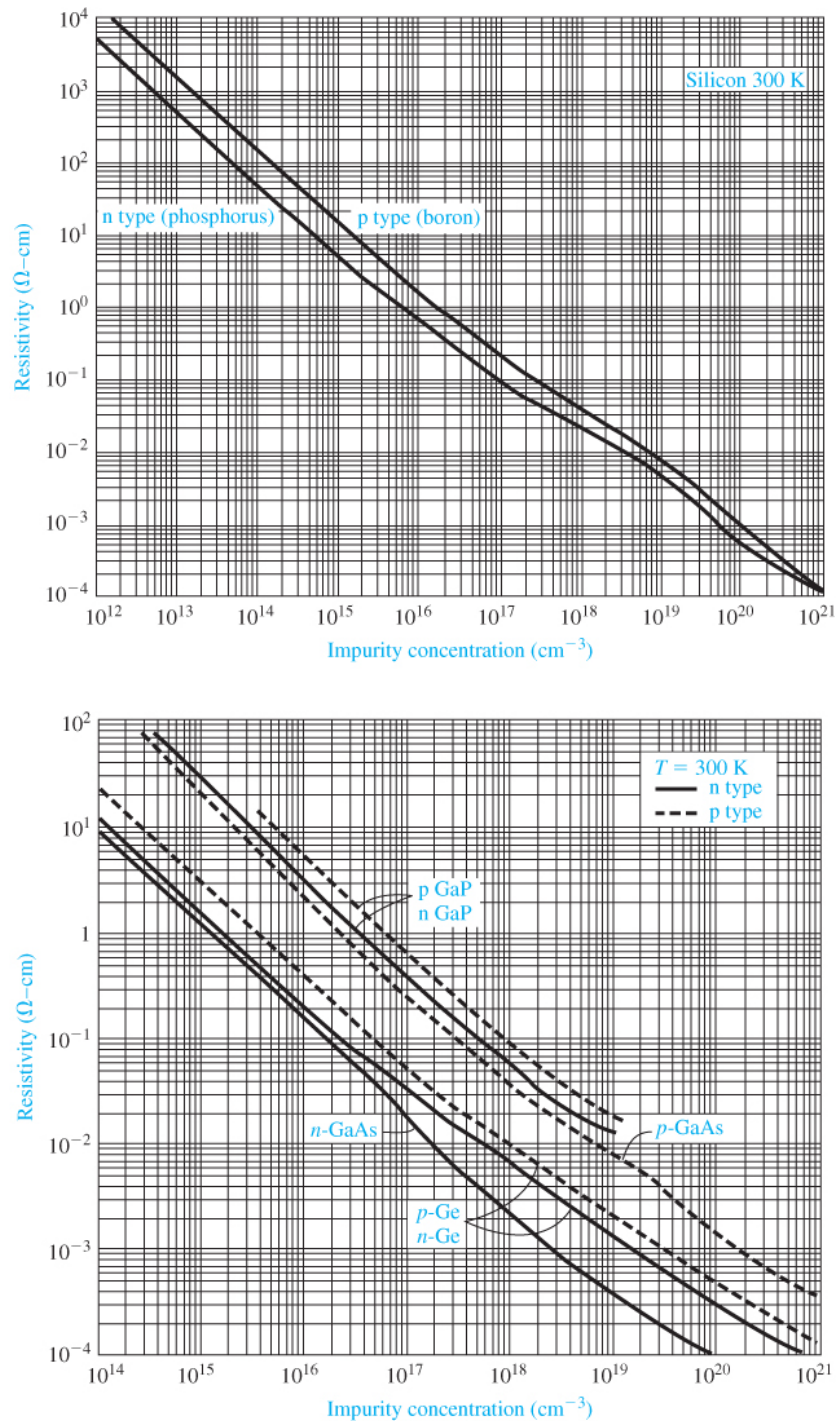


Figure 5.4 | Resistivity versus impurity concentration at $T = 300$ K in (a) silicon and (b) germanium, gallium arsenide, and gallium phosphide. (From Sze [14].)

- Note that the resistivities decrease as N_I increases due to increase in charge carriers.